

1983 IEEE Microwave and Millimeter Wave Monolithic Circuits Symposium May 31

HYNES AUDITORIUM MAIN HALL

Tuesday Morning

Tuesday Afternoon, May 31, 1983

I SIGNAL PROCESSING Chairman: C. Chao, Honeywell Corporate Technology Center, Bloomington, MN		III MILLIMETER WAVE CIRCUITS Chairman: B.E. Spielman, NRL, Washington, DC	
8:30 am	WELCOMING REMARKS Steering Committee Chairman: H.J. Kuno Hughes Aircraft Corp., Torrance, CA	1:15 pm	A TWO-STAGE MONOLITHIC BUFFER AMPLIFIER FOR 20 GHz SATELLITE COMMUNICATION W.C. Peterson and A.K. Gupta Rockwell International, Thousand Oaks, CA
8:45 am	HIGH QUALITY X-BAND MONOLITHIC DIODE MIXER A.W. Jacob-Hood and J.R. Smith GEC Research Laboratories, Wembley, England	1:35 pm	A GaAs MONOLITHIC PHASE SHIFTER FOR 30 GHz APPLICATION V. Sokolov, P. Bauhahn, J. Geddes, T. Contolatis, C. Chao Honeywell Corporate Technology Center, Bloomington, MN
9:05 am	WIDEBAND GaAs FOUR QUADRANT MULTIPLIER C. Ryan, D. Hartman, J.M. Fray, and C.E. Weitzel Motorola, Inc., Phoenix, AZ	1:55 pm	MONOLITHIC FREQUENCY DOUBLERS A. Chu, W.E. Courtney, L.J. Mahoney, R.A. Murphy, R.W. McClellan Lincoln Laboratory, Lexington, MA
9:25 am	A GaAs HIGH-SPEED COUNTER USING CURRENT MODE LOGIC K. Suyama, H. Suzuki, Y. Nemoto, S. Yamamura and M. Fukuta Fujitsu Ltd., Nakahara-ku, Kawasaki, Japan	2:15 pm	94 GHz MONOLITHIC GaAs BALANCED MIXERS C. Chao, A. Contolatis, S. Jamison, C. Butler Honeywell Corporate Technology Center, Bloomington, MN
9:45 am	BREAK	2:35 pm	BREAK
II DEVICE AND PROCESSING Chairman: R.A. Murphy, MIT Lincoln Laboratory, Lexington, MA		IV POWER AMPLIFIERS Chairman: R. Gilson, U.S. Army, Ft. Monmouth, NJ	
10:10 am	A GaAs/GaAs HETEROJUNCTION BALLISTIC BIPOLAR TRANSISTOR (BBT) FOR EHF AMPLIFIERS E.J. Zhu, W.H. Ku, and C.E.C. Wood Cornell University, Ithaca, NY	3:00 pm	A NEW, SPECIFICALLY MONOLITHIC APPROACH TO MICROWAVE POWER AMPLIFIERS D. Pavlidis, Y. Archambault, M. Effimerou, D. Kaminsky, A. Bert, J. Magarshack Thomson-CSF/DCM, Orsay, France
10:30 am	PROFILE STUDIES OF ION-IMPLANTED MESFETS J.M. Golio and R.J. Trew North Carolina State University, Raleigh, NC	3:20 pm	MONOLITHIC BROADBAND POWER AMPLIFIER AT X-BAND A. Platzker, M.S. Durschlag, J. Vorhaus Raytheon, Lexington, MA
10:50 am	LOW-NOISE MESFETS FOR ION-IMPLANTED GaAs MMICs A.K. Gupta, D.P. Su, K.T. Ip, and W.C. Peterson Rockwell International, Thousand Oaks, CA	3:40 pm	WIDEBAND 3W AMPLIFIER EMPLOYING CLUSTER MATCHING R.G. Freitag, J.E. Degenford, D.C. Boire, M.C. Driver, R.A. Wickstrom, C.D. Chang Westinghouse, Baltimore, MD
11:10 am	TRANSIENT CAPLESS ANNEALING OF ION-IMPLANTED PBNLEC GaAs FOR MONOLITHIC MICROWAVE INTEGRATED CIRCUITS R.C. Clarke, G.W. Eldridge, S.K. Wang and W.F. Valek Westinghouse R & D Center, Pittsburgh, PA	4:00 pm	2-20 GHz TRAVELING-WAVE POWER AMPLIFIER Y. Ayasli, L.D. Reynolds, R. Mozzi, J.L. Vorhaus, L. Hanes Raytheon, Lexington, MA
11:30 am	A NEW VIA HOLE STRUCTURE FOR POWER GaAs MESFETS and MMIC Li Songfa, Liu Qingxiang Hebei Semiconductor Research Institute, Shijiazhuang, China		

Wednesday Morning Session: See page 29, Session A. (also, page iv)